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Inc	losure	Material	:

Metal

Overall Length:

1.453 inches

Terminal Length:

0.450 inches

Overall Diameter:

0.667 inches

Mounting Facility Quantity:

1

Mounting Method:

Threaded stud

Cubic Measure:

2.030 cubic inches

Thready Qty Per Inch (tpi):

28

Thread Size:

0.125 inches

Criticality Code Justification:

Feat

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

400.0 emitter to collector voltage, floating potential, dc with base biased in reverse direction with respect to the collector

Current Rating Per Characteristic:

50.00 amperes peak forward surge current megahertz

Power Rating Per Characteristic:

50.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Special Features:

Nuclear hardness critical item; junction pattern arrangement: pn

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 1 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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